Limits of III-V nanowire growth based on particle dynamics

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Abstract

Crystal growth of III-V semiconductor nanowires assisted by a liquid particle/droplet occurs at the solid-liquid interface. This makes the stability of a droplet on the top of a nanowire crucial for successful nanowire growth. Using in-situ transmission electron microscopy together with theoretical analysis of the capillary forces involved, we conclude that truncation of the solid-liquid interface extend the stability range for a droplet in contact with the nanowire top interface. This provides insights to the limits of nanowire growth and is used to experimentally estimate the surface energy of the wurtzite \{11\bar{2}0\} facet of GaAs.

Epitaxial crystal growth of semiconductor nanowires assisted by a liquid-particle relies, in a simple perspective, on two fundamental principles: nucleation of material, and a liquid covering the growth front. As in many cases of crystal growth from a melt, the wetting angle, or the contact angle between the growing crystal and the melt, is of importance for crystal formation\cite{1,2}. For nanowires grown by the vapor-liquid-solid (VLS) mechanism, a fundamental stability criterion for having a droplet at the nanowire top has been proposed by Nebol’sin and Shchetinin\cite{3} based on ex-situ observations and earlier theoretical work\cite{4-6}. Since their report on this stability limit, several experimental\cite{7-11} and theoretical\cite{12-15} investigations of nanowire growth focusing on the wetting properties of the liquid metal catalyst have been reported, often with focus on its influence on nucleation\cite{8,9} rather than the droplet wetting dynamics. Still, this Nebol’sin-Shchetinin stability criterion remains generally accepted, perhaps due to the simplicity of the model.

The Nebol’sin-Shchetinin model predicts an upper bound for having a droplet on the top nanowire facet by relating the ratio of the surface energies of the solid and liquid phases in contact with the vapor (\(\gamma_{sv}\) and \(\gamma_{lv}\)) to the wetting angle and tapering of the nanowire\cite{3}. Although the model is widely accepted, it has important limitations: for instance growth of self-assisted GaAs\cite{16} and InAs\cite{17} have been extensively reported, although the relevant surface energy ratios are in these cases greater than the predicted upper bound (\(\gamma_{sv}/\gamma_{lv} \sim 2\) compared to \(\sqrt{2}\) for un-tapered nanowires\cite{3}). A limitation of the existing model is the assumption that the interface between droplet and nanowire is flat, which, according to experimental results\cite{8,9,18}, is not always the case during growth. These experimental reports have shown the formation of a truncation of the top nanowire facet during growth,
FIG. 1. The capillary forces pulling on a droplet, based on surface energies at the interfaces ($\gamma_{vs}$, $\gamma_{lv}$, $\gamma_{ls}$), are superimposed on a conventional transmission electron micrograph of a Au-droplet on top of a GaAs nanowire. The scalebar of the image represents 10 nm. This overview is accompanied by a schematic illustrating the angles used for orienting these forces with respect to each other; taking into account the dependence of truncation ($\psi$), tapering ($\delta$) and wetting angle ($90^\circ + \varphi$), which could be one of the reasons for the experimental and theoretical mismatch.

In this letter, we address the stability of the droplet wetting the nanowire top facet during growth, expanding on the Nebol’sin-Shchetinin stability criterion by introducing the possibility of forming a truncation of the interface. Given that the truncating facet has been observed to oscillate, both in size and truncation angle\cite{8, 18}, we also consider a lower limit of the surface energy ratio and wetting of a truncated droplet-nanowire interface to evaluate when different types of truncations would be probable. Our model is then compared to in-situ transmission electron microscopy (TEM) observations of a Au-Ga-droplet during crystal growth of a GaAs nanowire. By measuring the droplet wetting angle and estimating its surface tension, we demonstrate that the stability range for nanowire growth with a liquid droplet is extended by formation of a truncated interface.

To introduce the possibility of truncation into the stability condition for having a droplet on the top facet of a nanowire, we introduce further geometrical dependence for the balance of the capillary forces, as depicted in figure \ref{fig:1}, where the surface energy dependent capillary forces are oriented using tapering, wetting and truncation angles. The figure showcases an overview of the droplet nanowire system as well as the schematic angle relations between the surfaces. To balance the capillary forces, we consider all solid-vapor, liquid-vapor and solid-liquid interfaces to have the surface energies $\gamma_{sv}$, $\gamma_{lv}$ and $\gamma_{sl}$, respectively. The respective
orientation of the interfaces depends on the tapering angle ($\delta$), the wetting angle ($90^\circ + \varphi$) and the possible truncation cutting one of the corners at an angle of $\psi$. Balancing the horizontal forces laterally at the triple-phase boundary (arrows) in figure 1 provides a geometrical relation between the surface energies of the system according to

$$\gamma_{ls} \sin \psi = \gamma_{lv} \sin \varphi + \gamma_{sv} \sin \delta.$$  \hspace{1cm} (1)

Similarly, the vertical components of the forces are weighted, favoring a downward resulting force for studying the limits for a droplet to remain stable on the top facet,

$$\gamma_{ls} \cos \psi + \gamma_{lv} \cos \varphi < \gamma_{sv} \cos \delta.$$  \hspace{1cm} (2)

Elimination of $\gamma_{sl}$ provides the geometrical condition for the surface energy ratio when the droplet wets part of the nanowire sidewall (the solid-vapor interface),

$$\frac{\gamma_{sv}}{\gamma_{lv}} > \frac{\cos \varphi \sin \psi + \sin \varphi \cos \psi}{\cos \delta \sin \psi - \sin \delta \cos \varphi}.$$  \hspace{1cm} (3)

which reduces to $\gamma_{sv}/\gamma_{lv} > \cos \varphi$ for un-tapered nanowires with a flat growth interface ($\delta=0$ and $\psi=90^\circ$). Thus equation 3 represents a lower limit for the surface energy ratio.

For the droplet to remain stable on the top facet while having a downward resulting force requires that the resulting force must be directed upwards as soon as the liquid starts to wet the nanowire sidewall. If the resulting force continues to be downward, the droplet would be expected to be displaced from the top facet to the sidewall\[10, 19\]. Alternating the direction of the resulting force leads to a dynamic effect of the droplet by repeatedly forming and removing a truncation over time. This results in an upper bound for the surface energy ratio to allow the droplet to remain on the top facet and can be represented by following inequality,

$$\frac{\gamma_{sv}}{\gamma_{lv}} < \frac{\cos \varphi \sin \psi + \sin \varphi \cos \delta}{\cos \delta \sin \psi - \sin \delta \cos \varphi}.$$  \hspace{1cm} (4)

This ratio reduces to $\sin \varphi + \cos \varphi$ for un-tapered nanowires with a non-truncated interface between droplet and nanowire, just as in the original model\[3\]. The bounds presented, equations 3 and 4, are drawn in figure 2 for un-tapered nanowires with a flat growth interface and for truncated growth fronts ($\psi < 90^\circ$). Here it is evident that the truncation itself extends the stability limit for having a droplet on the top of a nanowire, or a pillar-like structure, allowing higher surface energy ratios than $\sqrt{2}$. 

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FIG. 2. A graph over the theoretically predicted lower and upper bound for having a particle on the top of a nanowire according to equation 3 and 4 for a truncation angle of 90° (black), 55° (blue), 45° (green) and 35° (red). We observe how the maximum allowed surface energy ratio increases as the truncation angle reduces. Note how the lower bound for 45° and 35° overlap with the upper bound for 90° and 45°, respectively.

To test the predictions of the model, (000\bar{1})-oriented Au-assisted wurtzite GaAs nanowires were grown in a transmission electron microscope (TEM) by supplying trimethyl-gallium (TMGa) and arsine to a SiNx grid, heated to 420 °C. When successively increasing the flow of Ga precursor, the size of the Au-Ga droplet was observed to increase as presented in figure 3a-b. The volume increase is attributed to Ga accumulation in the droplet, which in turn would lower its surface tension since the Au content remains the same and Ga has a lower surface tension. This allowed us to study several combinations of surface energy ratios and wetting angles, in order to test our model using growth parameters similar to previous reported work on Au-GaAs nanowire growth[20]. In order to compare the experimental observations of the droplet to the model, we extracted the volume of the droplet by measuring the projection of the droplet’s diameter and height using from conventional TEM recordings (detailed description is provided as supporting information). By assuming that only Ga contributes to the volume increase of the droplet, we extract the Ga-concentration in the droplet using a reference measurement done by X-ray energy dispersive spectroscopy of the same nanowire.

As the size of the droplet increases, we observe truncation of the liquid-solid interface as seen in figure 3c. However, this truncation is not always present during the conditions for our
growth as shown by the snapshot taken 2 s later, which is presented in figure 3a. Based on image recordings, provided as supplementary materials, we observe that the truncation size to change in time, similar to previous reports where it has been discussed to be connected to the droplet supersaturation[18]. In addition, we observe the average truncation angle to vary from $35^\circ$ to $55^\circ$ between truncation events. Based on the image recordings during GaAs nanowire growth as the Ga flow into the droplet was successively increased, we measured the wetting ($\varphi$) and tapering angle ($\delta$) as well as an estimation of the liquid tension based on the droplet volume. These parameters, along with the truncation angle ($\psi$), were used to compare our stability model in figure 2 with experimental data. For this comparison, we display the stability for a non-truncated interface facet and for the average experimental truncation angle ($45^\circ$) in figure 4.

FIG. 3. As the Ga flow is increased the Au-Ga droplet (darker contrast) is observed to increase its volume (a, b) during the TEM recording of the wurtzite crystal growth. As the droplet was allowed to expand, we observe a truncation of the edge of the interface between the nanowire and the droplet, indicated by arrows (b, c). However this is not always present but dynamically moves with the droplet and returns to a flat interface from time to time (d).

The experimental data, included in figure 4 as data points, have been extracted from measurements of the wetting angle and the estimate of the droplet volume from its two-dimensional projection. Assuming that the droplet is two-dimensional projection of a
spheroidal cap, and that any added volume to the droplet is pure Ga, allows for an estimation of the droplet composition for each frame of interest. The estimated change in droplet volume has been shown to provide a good indirect measurement of the change in composition of Au-Ga droplets during nanowire growth\cite{20}. From the composition, the surface tension is estimated by linear extrapolation from the pure species (Au and Ga), see supporting information for the details on the estimation. Each extracted data point is then related to whether a truncation has occurred within half a second or not, presented as green or black in figure \ref{fig:4}.

![Image](image.png)

**FIG. 4.** The surface energy ratio ($\gamma_{sv}/\gamma_{lv}$) as a function of droplet wetting angle ($\varphi + 90$) to the horizontal crystal facet. The dashed lines mark the lower and upper limit for having a droplet wetting the top facet for a un-tapered ($\delta = 0$) nanowire, with (green) and without (black) truncation. The accompanied data (hexagons) are the experimental result from the in-situ microscopy in this letter, measured both when a truncation are present (green) and not (black).

From the figure, we observe that the experimental observations of non-truncated interfaces (black) correlate with droplets having lower surface energy ratio ($\gamma_{sv}/\gamma_{lv}$) in comparison to most of the cases where truncation is present (green). On the other hand, there is an overlapping region for wetting angles above 120° where both truncated and non-truncated droplet-nanowire interfaces occur for similar surface energy ratios for certain angles. This is reasonable when taking into account that the interface is changing dynamically when forming or removing a truncation, and that the droplet does not change significantly in volume or shape within the 50 ms between the acquired images on which that the data. Further, we observed an increase probability of forming a truncation as the particle size increased.
The combination of experimental data and the stability model supports the idea that a truncation of the top facet could increase the stability for having a droplet wetting the top of a nanowire.

In figure 4, we have fitted the solid-vapor surface energy of the nanowire side-facet \( \{10\overline{1}0\} \) to 1.25 J/m\(^2\) based on existing theoretical calculations using unreconstructed surface (1.3 J/m\(^2\)\(^{[21]}\)) and density functional theory including surface reconstruction and passivation (0.40 < \( \gamma_{sv} \) < 1.06 J/m\(^2\)\(^{[22,24]}\)). For this value of the surface energy, we find that most of the data points for the non-truncated interface (black dots) fall below the predicted upper stability limit for this growth with a flat interface, while most of the data for the truncated interface (green dots) fall above this upper limit, and within the stability range for an interface with a truncation of 45°. Changes of this fitted surface energy \( \gamma_{sv} \) results in a vertical shift of the experimental data (plotted data), but not the drawn stability limits (graphs) as they depend on the geometrical orientation of the capillary forces. Lowering the surface energy by 0.1 J/m\(^2\) will shift all data down (0.08 units) and therefore also shift the data related to a truncation into the non-truncated region and vise versa if increased. Figures illustrating the data using a surface energy of 1.25 ± 0.1 J/m\(^2\) are provided as supporting information for visual reference. As a result of the parameter fitting, we could argue that the surface energy of the nanowire sidewall during growth is close to the expected value for an unreconstructed clean surface of the GaAs \( \{10\overline{1}0\}\)-surface\(^{[21]}\). The presented in-situ nanowire growth in combination with the proposed stability model is a way of experimentally estimating the surface energy of the solid-vapor interface of the nanowire side facet, narrowing down the large interval predicted from theoretical estimations.

To conclude, we have theoretically assessed the droplet stability on the top of a nanowire by addressing the possibility of forming a truncation of the droplet-nanowire interface. Experimentally, we have demonstrated a stability increase, allowing for larger ratios between the surface tension and solid surface energy as an effect of forming a truncation. Through comparisons to in-situ observations during Au-assisted growth of wurtzite GaAs nanowires we were able to evaluate the surface energies involved and estimate \( \gamma_{sv,10\overline{1}0} \) to 1.25 J/m\(^2\). This demonstrates that the combinations of in-situ growth observations and theoretical models is a powerful means to assess important material parameters for which there are wide variances in theoretical calculations and limited experimental validation.
Supporting Information (contact the authors for information)

Supporting information includes; (I) further details on the calculations for lower and upper boundary of the model (II) experimental details for the growth of wurtzite GaAs nanowires, (III) detailed description of the volume extraction and the conversion to liquid tension, (IV) comparative plots of the experimental data with lower and higher fixed $\gamma_{sv}$, and (V) supplementary movies showing the dynamic formation of a truncation.

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